

HiPerFET™ Power MOSFETs

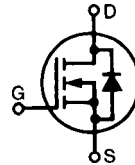
~~IXFH/IXFM 67 N10~~
~~IXFH/IXFM 75 N10~~

V _{DSS}	I _{D25}	R _{DS(on)}
100 V	67 A	25 mΩ
100 V	75 A	20 mΩ

t_{rr} ≤ 200 ns

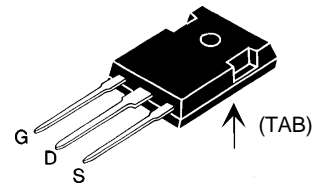
N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

Obsolete:
IXFM67N10
IXFM75N10



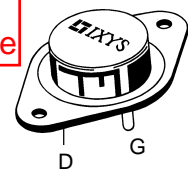
Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	100	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	100	V
V _{GS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	67N10	67 A
		75N10	75 A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	67N10	268 A
		75N10	300 A
I _{AR}	T _C = 25°C	67N10	67 A
		75N10	75 A
E _{AR}	T _C = 25°C	30	mJ
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	5	V/ns
P _D	T _C = 25°C	300	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C
M _d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	

TO-247 AD (IXFH)



~~TO-204 AE (IXFM)~~

Package
unavailable



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

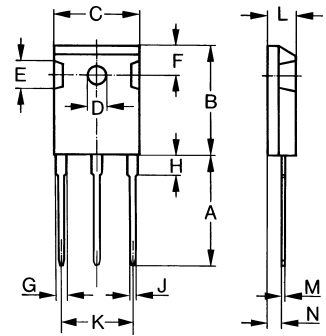
Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

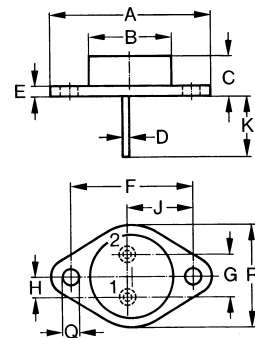
Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.0		4 V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±100 nA
I _{DSS}	V _{DS} = 0.8 • V _{DSS} V _{GS} = 0 V	T _J = 25°C		250 μA
		T _J = 125°C		1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	67N10		0.025 Ω
		75N10		0.020 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_{D25}$, pulse test	25	30	S	
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
C_{oss}			1600	pF	
C_{rss}			800	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External)		20	30	ns
t_r			60	110	ns
$t_{d(off)}$			80	110	ns
t_f			60	90	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		180	260	nC
Q_{gs}			36	70	nC
Q_{gd}			85	160	nC
R_{thJC}			0.42	K/W	
R_{thCK}		0.25		K/W	

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	67N10 75N10		67 A 75 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	67N10 75N10		268 A 300 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.75 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$ $V_R = 25\text{ V}$, $T_J = 125^\circ\text{C}$			200 ns 300 ns

TO-247 AD (IXFH) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-204 AE (IXFM) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	38.61	39.12	1.520	1.540
B	-	22.22	-	0.875
C	6.40	11.40	0.252	0.449
D	1.45	1.60	0.057	0.063
E	1.52	3.43	0.060	0.135
F	30.15	BSC	1.187	BSC
G	10.67	11.17	0.420	0.440
H	5.21	5.71	0.205	0.225
J	16.64	17.14	0.655	0.675
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R	25.16	26.66	0.991	1.050

Fig. 1 Output Characteristics

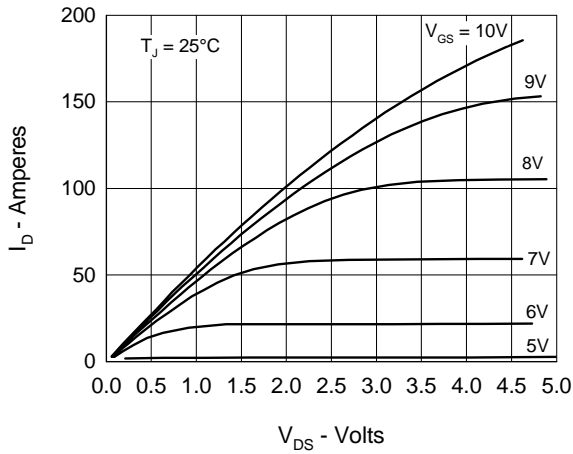


Fig. 2 Input Admittance

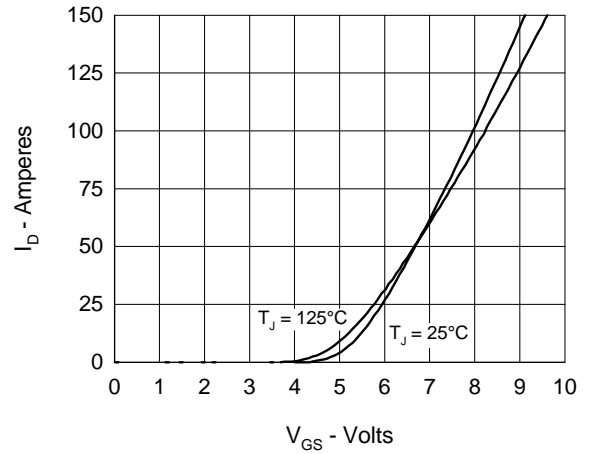


Fig. 3 $R_{DS(on)}$ vs. Drain Current

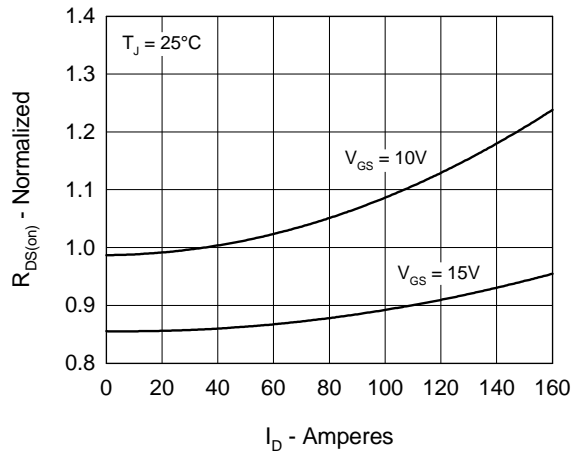


Fig. 4 Temperature Dependence of Drain to Source Resistance

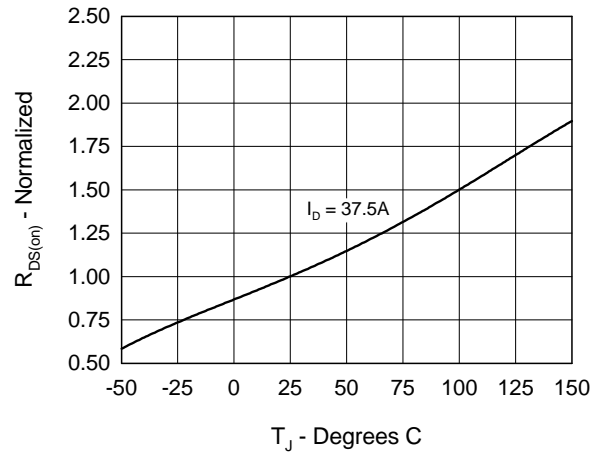


Fig. 5 Drain Current vs. Case Temperature

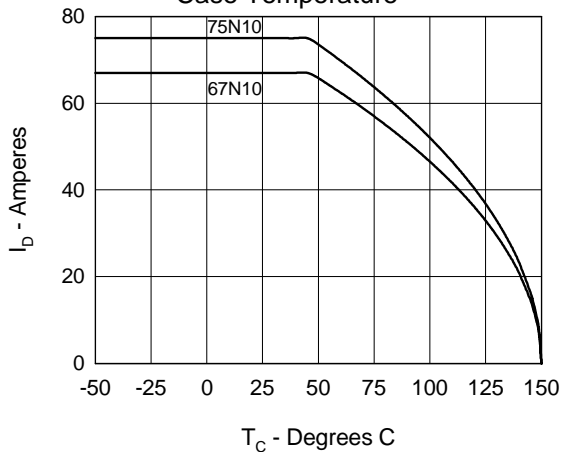


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

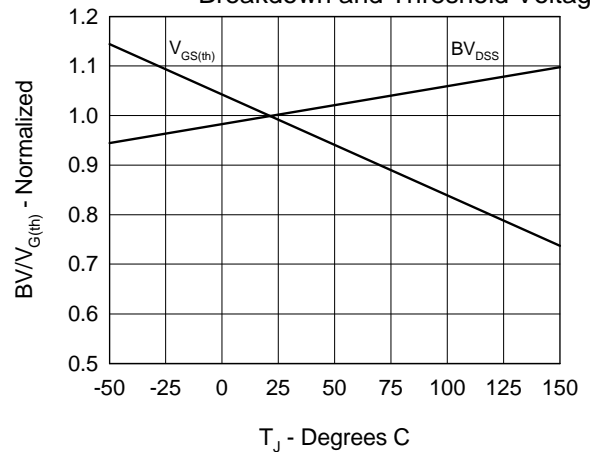
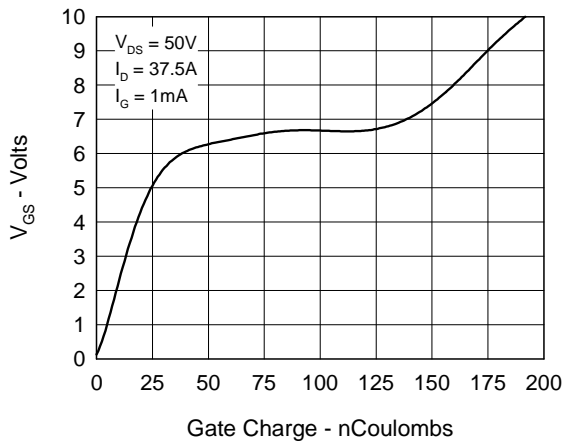
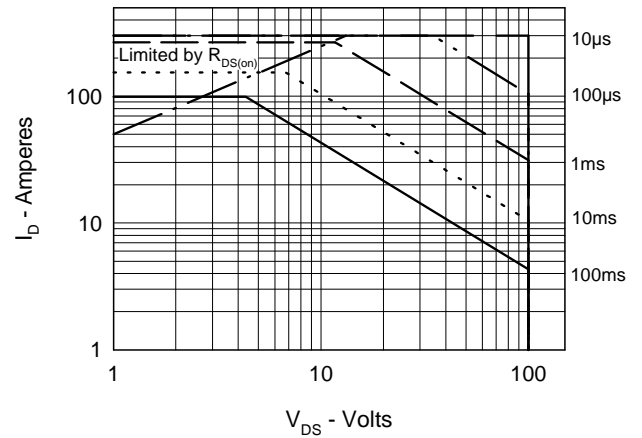
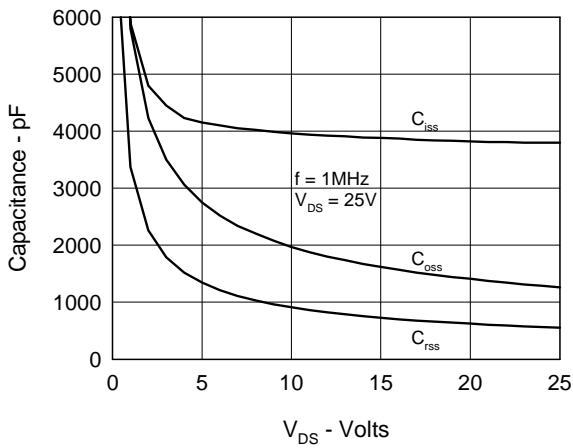
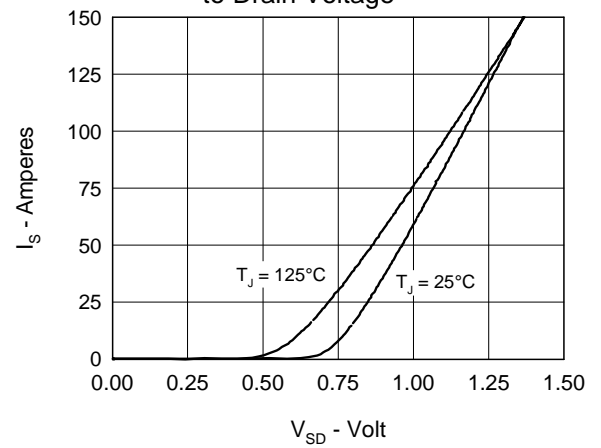


Fig.7 Gate Charge Characteristic Curve

Fig.8 Forward Bias Safe Operating Area

Fig.9 Capacitance Curves

Fig.10 Source Current vs. Source to Drain Voltage

Fig.11 Transient Thermal Impedance
